

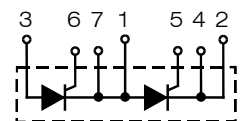
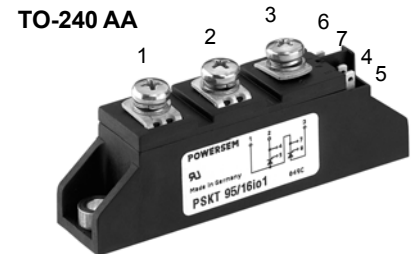
## Thyristor Modules Thyristor/Diode Modules

**PSKT 56**  
**PSKH 56**

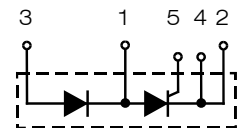
$I_{TRMS} = 2 \times 100 \text{ A}$   
 $I_{TAVM} = 2 \times 64 \text{ A}$   
 $V_{RRM} = 800-1800 \text{ V}$

Preliminary Data Sheet

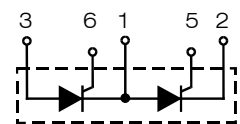
$V_{RSM}$ $V_{DSM}$	$V_{RRM}$ $V_{DRM}$	Type			
V	V	Version 1		Version 8	
900	800	PSKT 56/08io1	PSKH 56/08io1	PSKT 56/08io8	PSKH 56/08io8
1300	1200	PSKT 56/12io1	PSKH 56/12io1	PSKT 56/12io8	PSKH 56/12io8
1500	1400	PSKT 56/14io1	--	PSKT 56/14io8	PSKH 56/14io8
1700	1600	PSKT 56/16io1	PSKH 56/16io1	PSKT 56/16io8	PSKH 56/16io8
1900	1800	PSKT 56/18io1	--	PSKT 56/18io8	PSKH 56/18io8



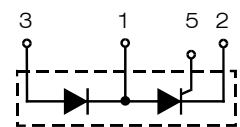
**PSKT  
Version 1**



**PSKH  
Version 1**



**PSKT  
Version 8**



**PSKH  
Version 8**

Symbol	Test Conditions	Maximum Ratings		
$I_{TRMS}^1, I_{FRMS}$ $I_{TAVM}^1, I_{FAVM}$	$T_{VJ} = T_{VJM}$ $T_C = 83^\circ\text{C}; 180^\circ \text{ sine}$ $T_C = 85^\circ\text{C}; 180^\circ \text{ sine}$	100 64 60	A A A	
$I_{TSM}^1, I_{FSM}$	$T_{VJ} = 45^\circ\text{C};$ $V_R = 0$ $t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	1500 1600	A A	
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$ $t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	11 200 10 750	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$	
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50 \text{ Hz}, t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.45 \text{ A}$ $di_G/dt = 0.45 \text{ A}/\mu\text{s}$	repetitive, $I_T = 150 \text{ A}$ non repetitive, $I_T = I_{TAVM}$	150 500	$\text{A}/\mu\text{s}$ $\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}^1$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$	1000	$\text{V}/\mu\text{s}$
$P_{GM}$	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$ $t_p = 300 \mu\text{s}$	10 5	W W
$P_{GAV}$			0.5	W
$V_{RGM}$			10	V
$T_{VJ}$			-40...+125	$^\circ\text{C}$
$T_{VJM}$			125	$^\circ\text{C}$
$T_{stg}$			-40...+125	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	3000 3600	V~ V~
$M_d$	Mounting torque (M5) Terminal connection torque (M5)		2.5-4.0/22-35 2.5-4.0/22-35	Nm/lb.in. Nm/lb.in.
<b>Weight</b>	Typical including screws		90	g

### Features

- International standard package, JEDEC TO-240 AA
- Direct copper bonded  $\text{Al}_2\text{O}_3$  -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 148688
- Gate-cathode twin pins for version 1

### Applications

- DC motor control
- Softstart AC motor controller
- Light, heat and temperature control

### Advantages

- Space and weight savings
- Simple mounting with two screws
- Improved temperature and power cycling capability
- Reduced protection circuits

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

Symbol	Test Conditions	Characteristic Values
$I_{RRM}, I_{DRM}$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	5 mA
$V_T, V_F$	$I_T, I_F = 200 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.57 V
$V_{T0}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )	0.85 V
$r_T$		3.7 m $\Omega$
$V_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	1.5 V
	$T_{VJ} = -40^\circ\text{C}$	1.6 V
$I_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	100 mA
	$T_{VJ} = -40^\circ\text{C}$	200 mA
$V_{GD}$	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.2 V
$I_{GD}$		10 mA
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	450 mA
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200 mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	2 $\mu\text{s}$
$t_q$	$T_{VJ} = T_{VJM}; I_T = 150 \text{ A}; t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ typ. $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	150 $\mu\text{s}$
$Q_S$	$T_{VJ} = T_{VJM}; I_T, I_F = 50 \text{ A}; -di/dt = 3 \text{ A}/\mu\text{s}$	100 $\mu\text{C}$
$I_{RM}$		24 A
$R_{thJC}$	per thyristor/diode; DC current per module	0.45 KW
$R_{thJK}$	per thyristor/diode; DC current per module	0.225 KW
	other values see Fig. 8/9	0.65 KW
		0.325 KW
$d_S$	Creepage distance on surface	12.7 mm
$d_A$	Strike distance through air	9.6 mm
$a$	Maximum allowable acceleration	50 m/s <sup>2</sup>

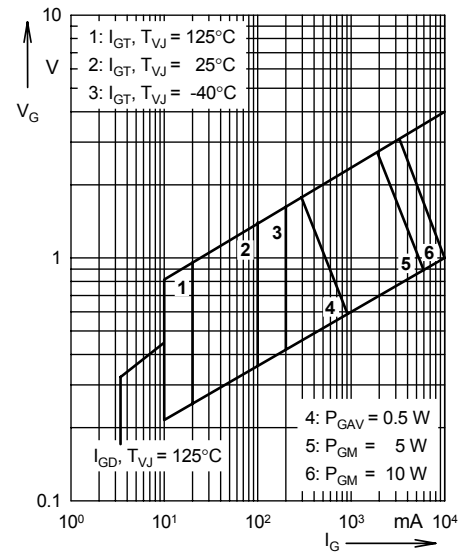


Fig. 1 Gate trigger characteristics

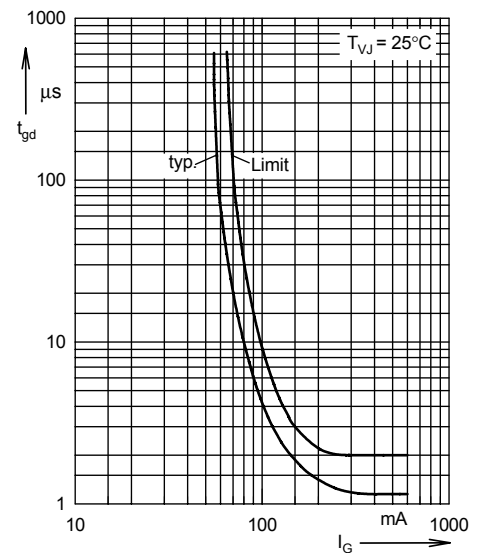
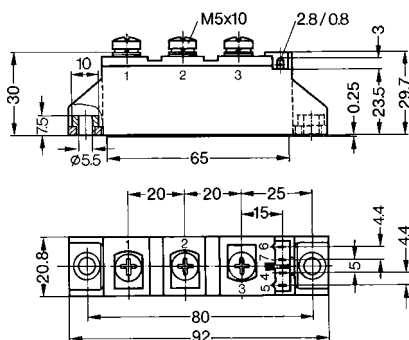


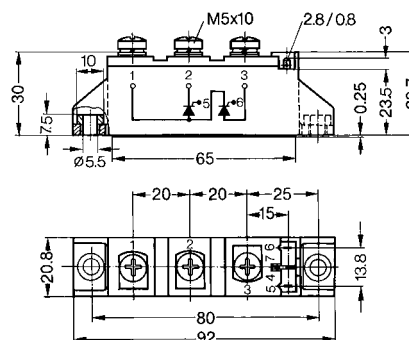
Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")

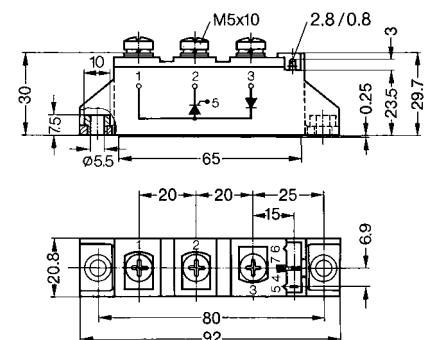
### PSKT/PSKH Version 1



### PSKT Version 8



### PSKH Version 8



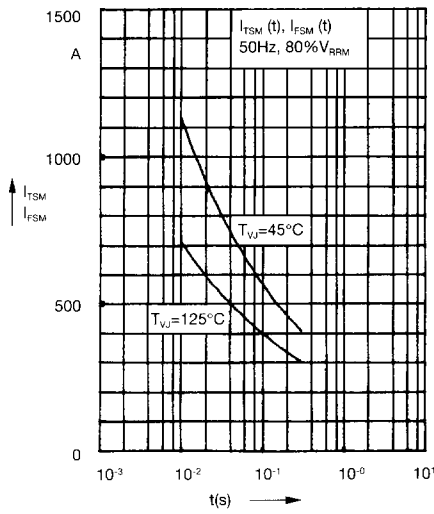


Fig. 3 Surge overload current  
 $I_{TSM}, I_{FSM}$ : Crest value,  $t$ : duration

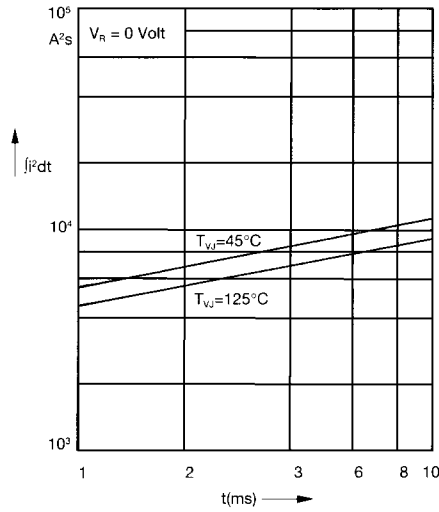


Fig. 4  $\int i^2 dt$  versus time (1-10 ms)

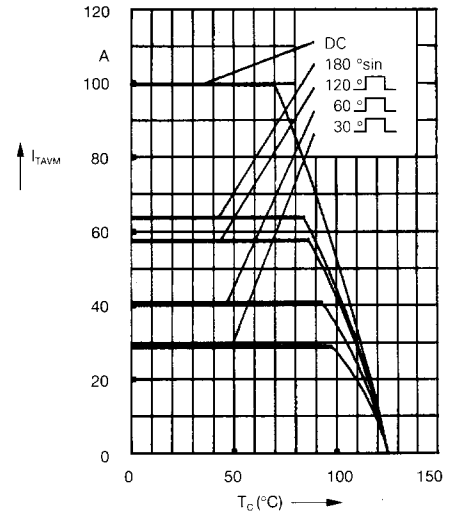


Fig. 4a Maximum forward current at case temperature

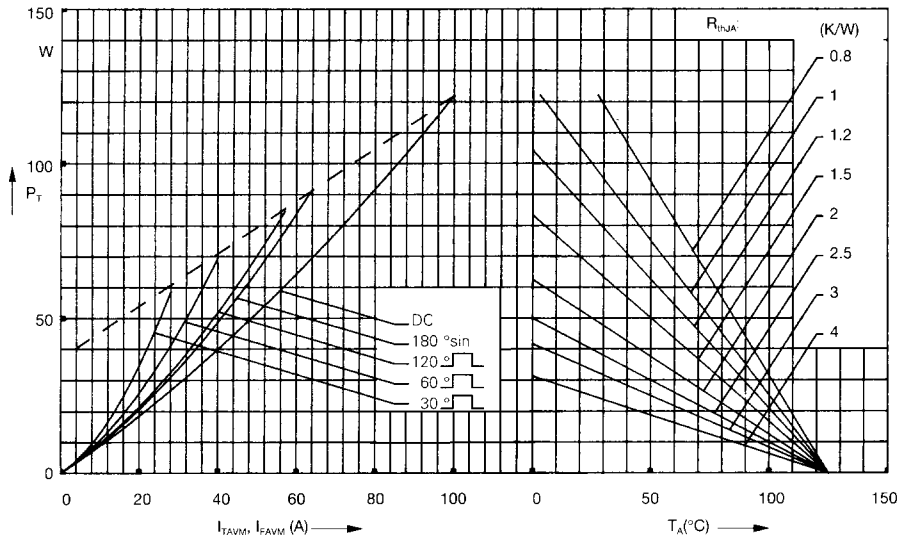


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

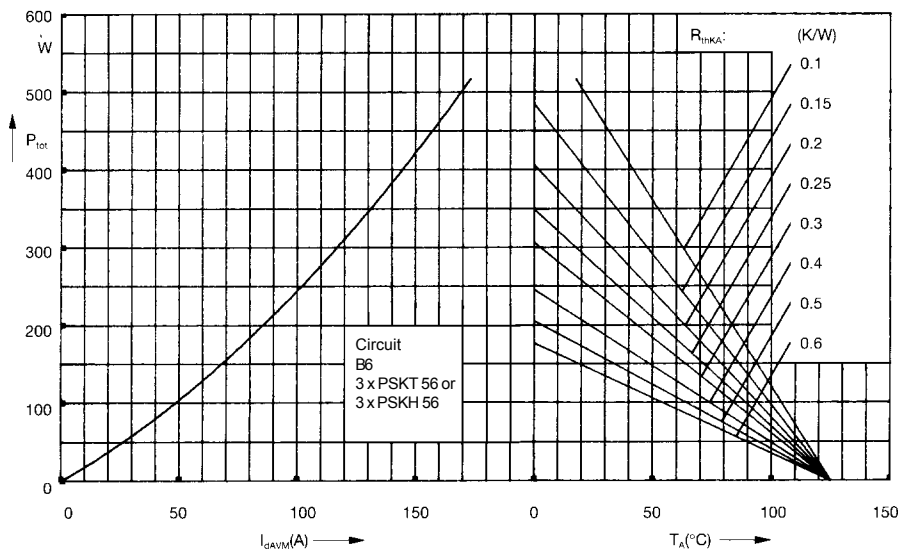


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

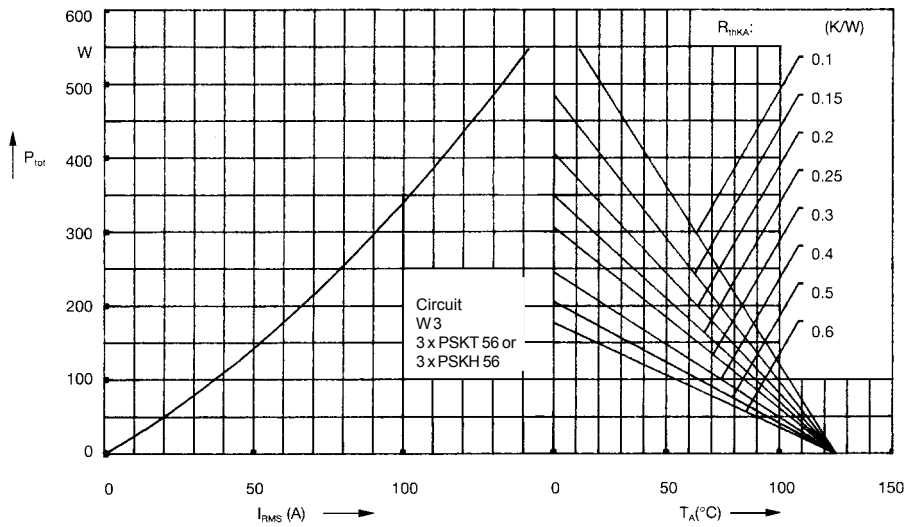


Fig. 7 Three phase AC-controller:  
Power dissipation versus RMS  
output current and ambient  
temperature

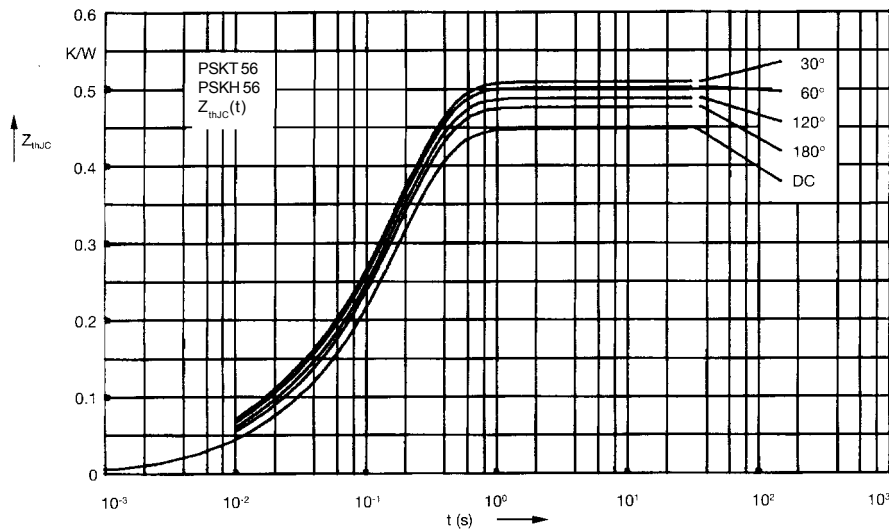


Fig. 8 Transient thermal impedance  
junction to case (per thyristor or  
diode)

$R_{thJC}$  for various conduction angles d:

d	$R_{thJC}$ (K/W)
DC	0.45
180°	0.47
120°	0.49
60°	0.505
30°	0.52

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.014	0.015
2	0.026	0.0095
3	0.41	0.175

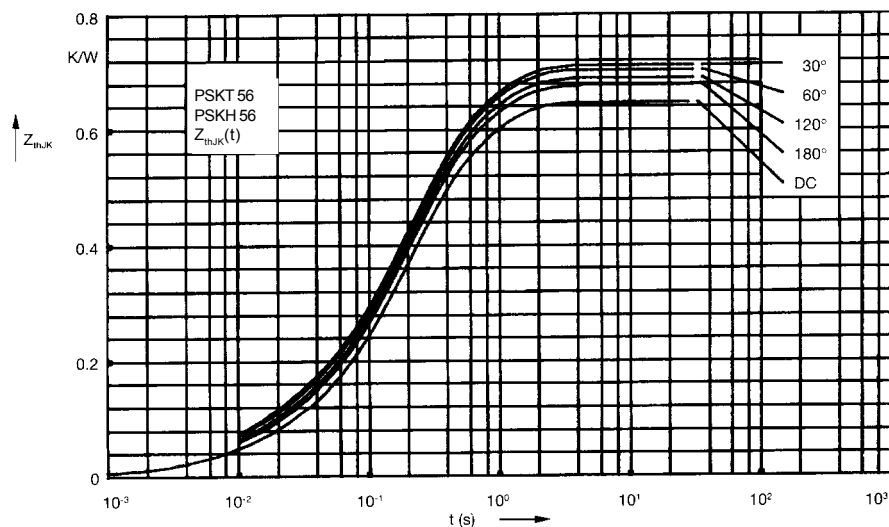


Fig. 9 Transient thermal impedance  
junction to heatsink (per thyristor  
or diode)

$R_{thJK}$  for various conduction angles d:

d	$R_{thJK}$ (K/W)
DC	0.65
180°	0.67
120°	0.69
60°	0.705
30°	0.72

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.014	0.015
2	0.026	0.0095
3	0.41	0.175
4	0.2	0.67